

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	680	(scrub or scrubbing) and plasma and (etch or etching) and semiconductor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:44
2	BRS	L3	335	photoresist and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:45
3	BRS	L4	35664	(plasma adj etch) or (plasma adj etching)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:45
4	BRS	L5	304	4 and 1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:45
5	BRS	L6	178	photoresist and 5	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L7	17734	photoresist same plasma	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:46
7	BRS	L8	304	1 and 5	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:46
8	BRS	L9	2694	low-k	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:46
9	BRS	L10	8	9 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:47
10	BRS	L12	7	wet and 10	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/02/10 15:47